Abstracts

Zero Power Consumption Si/SiGe HBT SPDT T/R Antenna Switch

R. Gotzfried, T. Itoh, J.F. Luy and H. Schumacher. "Zero Power Consumption Si/SiGe HBT SPDT T/R Antenna Switch." 1996 MTT-S International Microwave Symposium Digest 96.2 (1996 Vol. II [MWSYM]): 651-654.

Design and performance of a new transmit/receive (T/R) antenna switch for mobile communication systems at 1.8GHz using Si/SiGe Heterojunction Bipolar Transistors (HBT) are described. The switch is designed to be a part of a transceiver front end for DECT and DCS 1800 applications. This circuit requires no external DC bias. The insertion loss in the receive arm is <1.5dB and the isolation >25dB at the operating frequency.

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